

Homework #8 Solutions

1(a) MOS Transistor: Bulk: $N_A = 10^{18} \text{ cm}^{-3}$

$$x_{ox} = 4 \text{ nm} = 4 \times 10^{-7} \text{ cm}$$

$$W = 2L = 10^{-4} \text{ cm} = 1 \mu\text{m}$$

Ignore Oxide Charges

Find V_{th} @ $V_{SB} = 0$:

$$V_{th} = \phi_{ms} - 2\phi_F - \frac{Q_B'}{C_{ox}'}$$

$$C_{ox}' = \frac{\kappa_{ox} \epsilon_0}{x_{ox}} = \frac{(3.9)(8.85 \times 10^{-14} \text{ F cm}^{-1})}{4 \times 10^{-7} \text{ cm}} = \underline{\underline{8.6 \times 10^{-7} \text{ F cm}^{-2}}}$$

$$\phi_F = -\frac{kT}{q} \ln\left(\frac{N_A}{n_i}\right) = -0.0256 \ln\left(\frac{10^{18}}{10^{10}}\right) \text{ V} = \underline{\underline{-0.4727 \text{ V}}}$$

$$Q_B' = -\sqrt{2\kappa_S \epsilon_0 q N_A |2\phi_F|} = \underline{\underline{-5.59 \times 10^{-7} \text{ C cm}^{-2}}}$$

$$\phi_{ms} = \chi_S - \left(\chi_S + \frac{E_g}{2} + | \phi_F | \right) = -\left(\frac{E_g}{2} + | \phi_F | \right) = \underline{\underline{-1.03 \text{ V}}}$$

$$V_{th} = -1.03 + 0.4727 + \frac{5.59 \times 10^{-7} \text{ C cm}^{-2}}{8.6 \times 10^{-7} \text{ F cm}^{-2}} = \underline{\underline{0.564 \text{ V}}}$$

1b) To use the equation given, we need to find Q_d^{max}

$$Q_d^{max} = -\sqrt{2\kappa_S \epsilon_0 q N_A |V_{CB} - 2\phi_F|}$$

$$C_S^{\text{depl}} = \frac{d Q_d^{\text{max}}}{d V_{CB}} = \frac{1}{2} \sqrt{\frac{2 K_S \epsilon_0 q N_A}{|V_{CB} - 2 \phi_F|}} \quad V_{CB} = 0$$

$$\alpha = \frac{C_s^{\text{depl}}}{C_{ox'}} = \frac{1}{2C_{ox'}} \left(\frac{2k_s \epsilon_0 q N_A}{2\phi_F} \right)^{\frac{1}{2}} = \underline{\underline{0.34}}$$

1d) i) $V_S = 0$ $V_B = 0V$ $V_G = 3V$ $V_D = 1V$

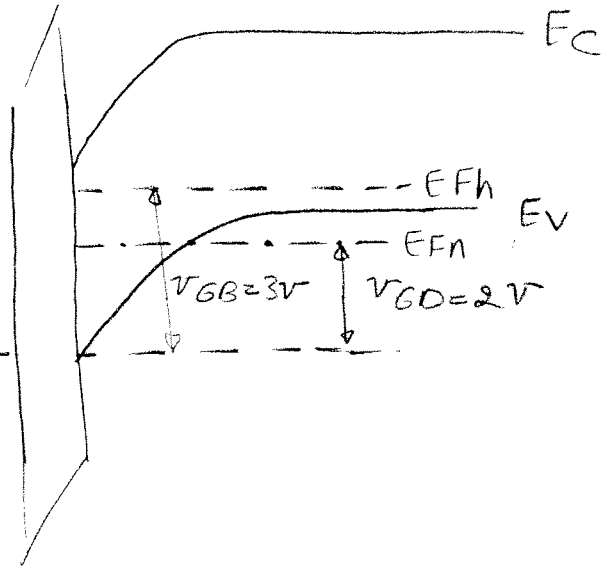
$V_G > V_{th} \Rightarrow$ Device is ON

$$V_{OS, Sat} = \frac{V_{GS} - V_{th}}{1 + \alpha} = \frac{3 - 0.564}{1 + 0.34} = 1.82V$$

$V_{DS} < V_{DS,sat} \implies$ Device is in linear region

$$I_D = \frac{W}{L} \mu_n' C_{ox}' \left[(V_{GS} - V_{th}) V_{DS} - \frac{1}{2} (1 + \alpha) V_{DS}^2 \right] = \underline{\underline{0.380 \text{ mA}}}$$

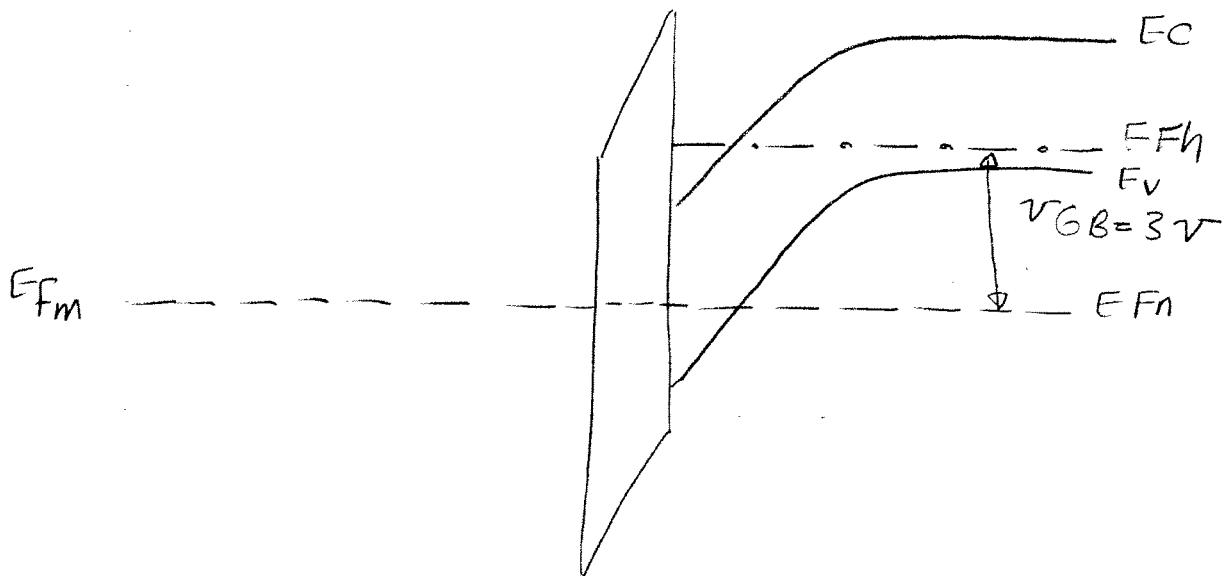
$$\begin{aligned} E_{\text{eff}} &= \frac{V_g + V_t + 0.2}{6 t_{\text{ox}}} \\ &= 1.56 \text{ MV/cm} \\ \Rightarrow \mu_n' &= 125 \frac{\text{cm}^2}{\text{Vs}} \end{aligned}$$



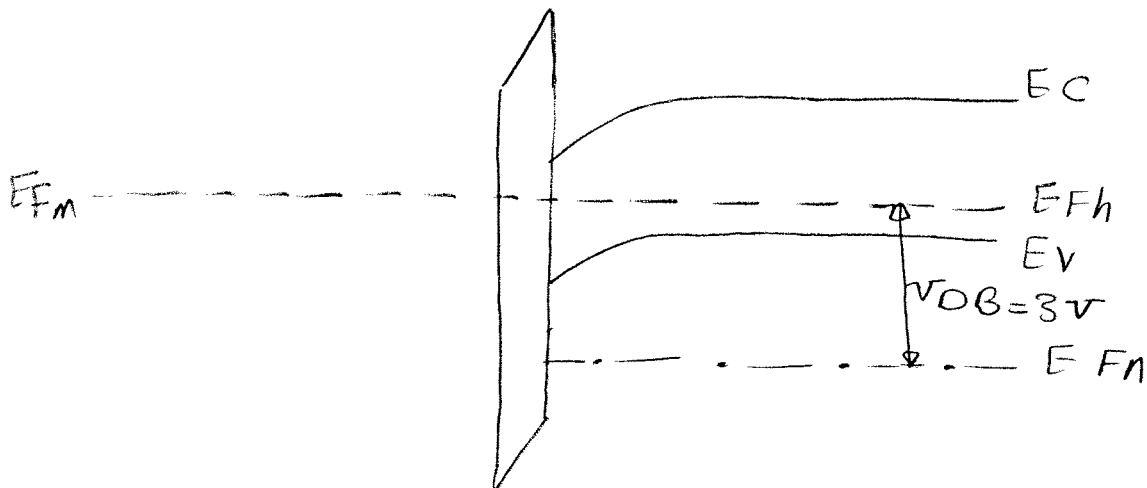
1d) ii) $V_S = 0V$, $V_B = 0V$, $V_C = 3V$, $V_D = 3V$

Device is ON and is in the Saturation region

$$I_D = \frac{w}{L} \mu_n' C_{ox} \left[\frac{(V_{GS} - V_{th})^2}{2(1+\alpha)} \right] = \underline{\underline{0.476 \text{ mA}}}$$



1d) iii) $V_S = 0$, $V_B = 0V$, $V_G = 0V$, $V_D = 3V$
 $V_G < V_{th} \Rightarrow$ Device is OFF $\Rightarrow I_D = 0$





2 a) MOS P-channel, $V_{th} = -0.4V$ $SIB = 0V$

$$V_G = -3V \quad V_D = -2V \quad X_{ox} = 10 \times 10^{-7} \text{ cm} = 10^{-6} \text{ cm}$$

$$N_d = 10^{17} \text{ cm}^{-3} \quad w/L = 2$$

Find V_{FB} :

$$V_{th} = V_{FB} - 2\phi_F - \frac{Q_B'}{C_{ox}'} \quad \textcircled{1}$$

$$\phi_F = \frac{kT}{q} \ln \left(\frac{N_d}{n_i} \right) = 0.0256V \ln \left(\frac{10^{17}}{10^{10}} \right) = \underline{\underline{0.41V}}$$

$$Q_B' = \sqrt{2k_s \epsilon_0 q N_d |2\phi_F|} = 1.65 \times 10^{-7} \text{ C cm}^{-2}$$

$$C_{ox}' = \frac{(3.9)(8.85 \times 10^{-14} \text{ F cm}^{-1})}{10^{-6} \text{ cm}} = \underline{\underline{3.45 \times 10^{-7} \text{ F cm}^{-2}}}$$

$$\textcircled{1} \Rightarrow -0.4V = V_{FB} - 2(0.41)V - \frac{(1.67 \times 10^{-7} \text{ C cm}^{-2})}{3.45 \times 10^{-7} \text{ F cm}^{-2}}$$

$$\Rightarrow \underline{\underline{V_{FB} = 0.9V}}$$

2 b) PMOS $\Rightarrow V_g < V_{th} \Rightarrow$ Device is ON

$$\alpha = \frac{1}{2C_{ox}} \left(\frac{2k_s \epsilon_0 q N_d}{2\phi_F} \right)^{\frac{1}{2}} = \underline{\underline{0.29}}$$

$$V_{DS, sat} = \frac{V_G - V_{th}}{1 + \alpha} = \underline{\underline{-2.02V}}$$

$V_{DS} > V_{DS, sat} \Rightarrow$ Linear Region

$$2c) I_D = \frac{w}{L} \mu_p' C_{ox}' \left[(V_{GS} - V_{th}) V_{DS} - \frac{1}{2} (1+\alpha) V_{DS}^2 \right]$$

$$E_{eff} = \frac{V_g + V_t - 2.3V}{6 \times 0.001} = -0.95 \text{ MV cm}^{-1} \Rightarrow \mu_p' \approx 50 \frac{\text{cm}^2}{\text{Vs}}$$

$$\Rightarrow I_D = \underline{\underline{0.0897 \text{ mA}}}$$

2d)

$$V_{th} = V_{FB} - 2\phi_F - \frac{\sqrt{2k\epsilon_0 q N_d |V_{SB} - 2\phi_F|}}{C_{ox}'}$$

$$V_{DS} = V_{DS, \text{sat}} = \frac{V_{GS} - V_{th}}{1+\alpha}$$

$$\Rightarrow (1.291)(-2) = -3 - V_{th}$$

$$\Rightarrow V_{th} = -3 + 2 \times 1.29 = -0.42 \text{ V}$$

$$\Rightarrow -0.42 = 0.9 - 0.82 - (|V_{SB} - 0.82|)^{\frac{1}{2}} (0.53)$$

$$\Rightarrow V_{SB} - 0.82 = -0.88 \Rightarrow V_{BS} = 0.07 \text{ V}$$

And the device will go to the Saturation mode.

$$2e) V_{SB} = 0 \text{ V} \quad N' = 10^{12} \text{ cm}^{-2}$$

$$\Delta V_{th} = \frac{-qN'}{C_{ox}'} = - \frac{(1.6 \times 10^{-19} \text{ C})(10^{12} \text{ cm}^{-2})}{3.45 \times 10^{-7} \text{ F cm}^{-2}} = \underline{\underline{-0.46 \text{ V}}}$$

$$\left. \begin{aligned} V_{th, \text{new}} &= -0.4 - 0.46 \text{ V} = \underline{\underline{-0.86 \text{ V}}} \\ V_{DS, \text{sat}} &= \frac{V_{GS} - V_{th, \text{new}}}{1+\alpha} = \underline{\underline{-1.66 \text{ V}}} \end{aligned} \right\} \Rightarrow \text{Device is ON and is in Saturation}$$

$$3) L = 0.1 \mu\text{m} = 10^{-5} \text{ cm} \quad V_{DS} = V_{DS, \text{sat}} + 0.4 \text{ V}$$

$$I_D = 10^{-6} \text{ A} \quad N_A = 2 \times 10^{18} \text{ cm}^{-3}$$

⇒ Device is in Saturation:

$$\xrightarrow[\text{from the note.}]{\text{Equation 16}} \Delta L \approx \sqrt{\frac{2k_s \epsilon_0}{q N_A} |V_{DS} - V_{DS, \text{sat}}|} = \underline{\underline{1.62 \times 10^{-6} \text{ cm}}}$$

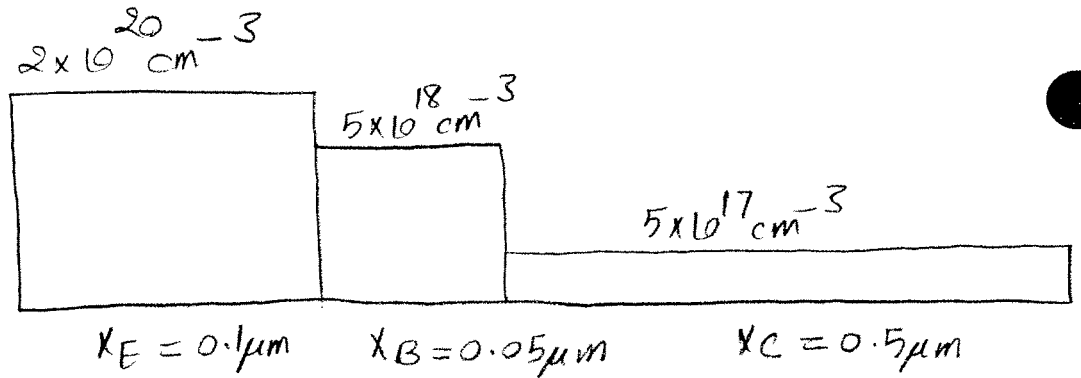
$$I_D' = \left(\frac{L}{L - \Delta L} \right) I_D = \left(\frac{10^{-5}}{10^{-5} - 1.62 \times 10^{-6}} \right) \times 10^{-6} \text{ A} \approx 1.19 \times 10^{-6} \text{ A}$$

$$g_{d, \text{sat}} = \frac{1}{R_{\text{out}}} = \frac{I_D' - I_D}{\Delta V_{DS}} = \frac{0.19 \mu\text{A}}{0.4 \text{ V}} = 4.75 \times 10^{-7} \text{ S}$$

$$\Rightarrow \underline{\underline{R_{\text{out}} = 2.11 \text{ M}\Omega}}$$

It is also possible to calculate the output resistance in saturation (R_{out} or r_{ds}) by differentiating for I_{DS}' above with respect to V_{DS} (via dependence of ΔL on V_{DS}). The result is the small signal output resistance about the operating point specified ($V_{DS} - V_{DS, \text{sat}} = 0.4 \text{ V}$) rather than the average output resistance in saturation over the range of $0 < V_{DS} - V_{DS, \text{sat}} < \infty$ as calculated above.

4a)



$$\alpha_F = \frac{I_C}{I_E} = \alpha_T \gamma \quad \gamma \text{ is 1 because there is no recombination}$$

$$D_{PE} = 1 \text{ cm}^2/\text{s} \quad D_{nB} = 5 \text{ cm}^2/\text{s} \quad D_{pC} = 6.5 \text{ cm}^2/\text{s}$$

$$L_{nB} = \sqrt{D_{nB} \tau_{nB}} = \sqrt{5 (0.5 \mu s)} = \underline{\underline{16 \mu m}}$$

$$\alpha_T \approx 1 - \frac{x_B^2}{2(L_{nB})^2} = 1 - \frac{(0.05 \times 10^{-4})^2}{(16 \times 10^{-4})^2} \quad \leftarrow \text{True because } x_B \ll L_{nB}$$

$$= 0.99999 \approx 1 \Rightarrow \alpha_F \approx \gamma_F$$

$$\alpha_F = \gamma_F = \frac{1}{1 + \frac{x_B}{x_E} \frac{N_{AB}}{N_{DE}} \frac{D_{PE}}{D_{nB}}} = \frac{1}{1 + \frac{0.05 \mu m}{0.1 \mu m} \frac{5 \times 10^{18}}{2 \times 10^{20}} \times \frac{1}{5}}$$

$$= \underline{\underline{0.9925}}$$

$$\beta_F = \frac{\alpha_F}{1 - \alpha_F} = \underline{\underline{40.0}}$$

4a) From equation (38):

$$\alpha_{12} = \alpha_F I_{ES} \Rightarrow \frac{q A D_{nB} n_i^2}{x_B N_{aB}} = \alpha_F I_{ES}$$

$$\Rightarrow J_{ES} = \frac{q D_{nB} n_i^2}{x_B \alpha_F N_{aB}} = \frac{(1.6 \times 10^{-19} \text{ C})(5 \text{ cm}^2/\text{s})(10^{20} \text{ cm}^{-3})}{(0.05 \times 10^{-4} \text{ cm})(0.9925)(5 \times 10^{18} \text{ cm}^{-3})}$$

$$= \underline{\underline{3.22 \times 10^{-12} \text{ A cm}^{-2}}}$$

4b) $\alpha_R = \alpha_T \gamma_R \approx \gamma_R$

$$\gamma_R = \frac{1}{1 + \frac{x_B}{x_C} \frac{D_{pC}}{D_{nB}} \frac{N_{aB}}{N_{dC}}} = \frac{1}{1 + \frac{(0.05 \mu\text{m})}{(0.5 \mu\text{m})} \times \frac{6.5}{5} \times \frac{5 \times 10^{18}}{5 \times 10^{17}}}$$

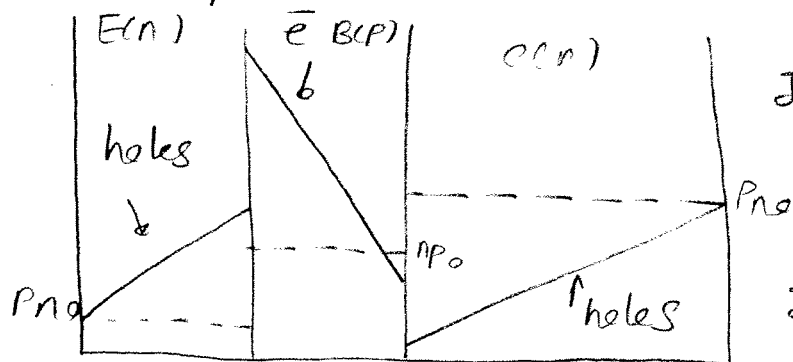
$$= \underline{\underline{0.435}}$$

$$\beta_R = \frac{\alpha_R}{1 - \alpha_R} = 0.769$$

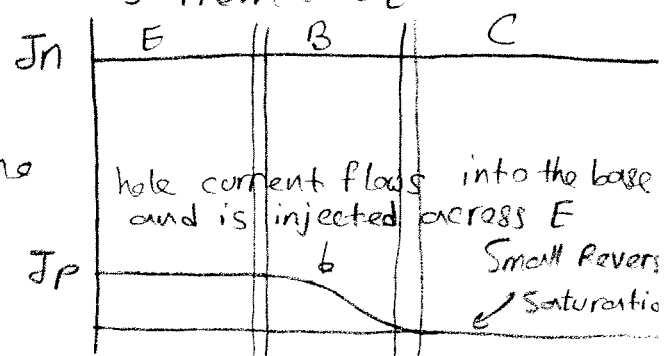
$$\alpha_{12} = \alpha_R I_{CS} \Rightarrow I_{CS} = \underline{\underline{7.35 \times 10^{-12} \text{ A cm}^{-2}}}$$

4c) For (a), forward active.

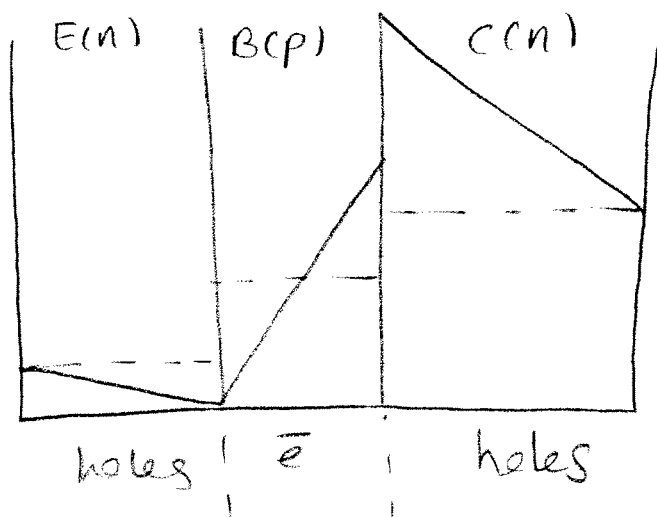
Minority Charge Densities



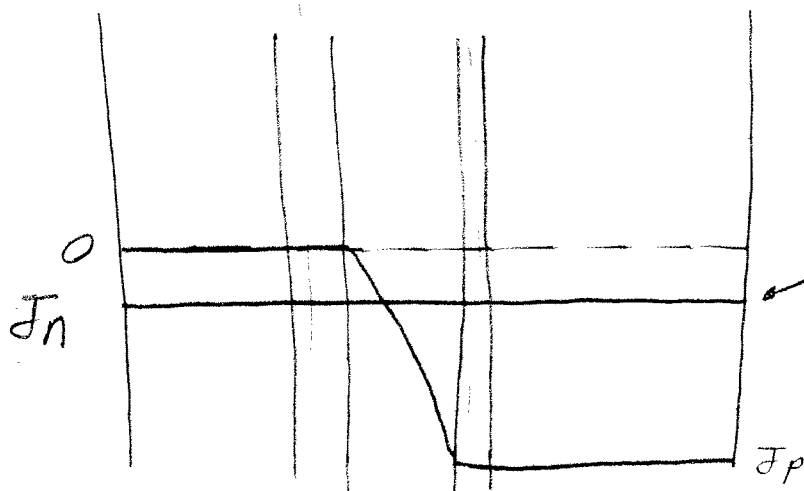
Positive Current direction defined as From C $\rightarrow$ E



For (b) reverse active:



Minority Charge Density



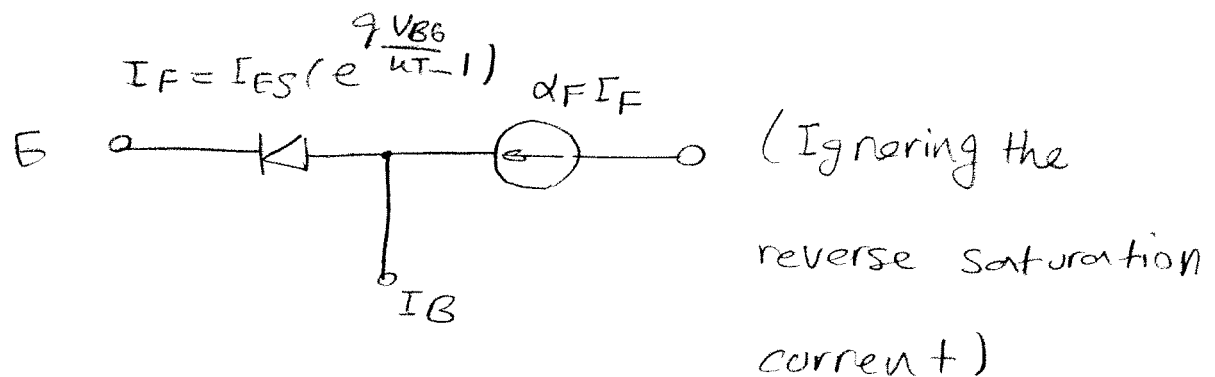
J_n is now negative

- J positive direction is $C \rightarrow E$
- $J_{pe} > J_n$ Since $\alpha_R \ll 1$
- $J_n \approx \text{Constant} \therefore \alpha_T \approx 1$

$$4d) A_E = A_C = 10^{-5} \text{ cm}^2$$

$$I_B = 1 \mu\text{A} \quad V_{CE} = 3 \text{ V}$$

Assume that we are in the forward active mode ($V_{BE} > 0$ $V_{BC} < 0$)



$$\Rightarrow \alpha_F I_F + I_B = I_F$$

$$\Rightarrow (0.9925) I_F + 1 \mu\text{A} = I_F$$

$$\Rightarrow 7.5 \times 10^{-3} \times I_F = 1 \mu\text{A} \Rightarrow I_F = 1.33 \times 10^{-4} \text{ A}$$

$$\Rightarrow I_C = \alpha_F I_F = \underline{\underline{0.132 \text{ mA}}}$$

Checking the assumption:

$$I_{ES} = J_{ES} \times A_E = 3.22 \times 10^{-12} \times 10^{-5} = 3.22 \times 10^{-17}$$

$$\Rightarrow I_F = 1.33 \times 10^{-4} = 3.22 \times 10^{-17} (e^{\frac{qV_{BE}}{kT}})$$

$$\Rightarrow V_{BE} = \underline{\underline{0.74 \text{ V}}} \text{ and } V_{BC} = \underline{\underline{-2.26 \text{ V}}} \text{ Ok!}$$

